WG2302

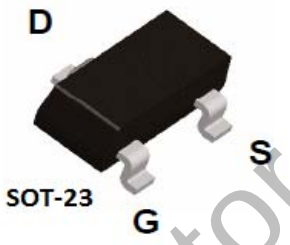
20V N-Channel MOSFET

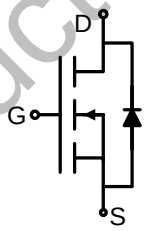
Features:

- ☐ Low Intrinsic Capacitances.
- ☐ Excellent Switching Characteristics.
- ☐ Extended Safe Operating Area.
- ☐ Unrivalled Gate Charge :Qg= 10nC (Typ.).
- ☐ BVDSS=20V,I_D=4.0A
- ☐ R_{DS}(on) : 50mΩ (Max) @V_G=2.5V
- ☐ 100% Avalanche Tested

SOT-23

RoHS COMPLIANT





MARKING:**A2SHB**

Schematic diagram

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	3.0	A
Drain Current-Pulsed (Note 1)	I_{DM}	10	A
Maximum Power Dissipation	P_D	1.0	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	125	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±12V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	0.45	0.65	1.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=2.5V, I_D=3.5A	-	37	50	mΩ
		V_{GS}=4.5V, I_D=4.5A	-	30	40	mΩ
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=10V,V_{GS}=0V, F=1.0MHz	-	405	-	PF
Output Capacitance	C_{oss}		-	75	-	PF
Reverse Transfer Capacitance	C_{rss}		-	55	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=10V, R_L=2.7Ω V_{GS}=4.5V,R_{GEN}=3Ω	-	11	-	nS
Turn-on Rise Time	t_r		-	35	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	V_{DS}=10V,I_D=3.0A, V_{GS}=2.5V	-	3.3	-	nC
Gate-Source Charge	Q_{gs}		-	0.7	-	nC
Gate-Drain Charge	Q_{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=4.0A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-		4.0	A

Typical Characteristics